



#6/c 6/10/03
RECEIVED
JUN 03 2003
TC 1700

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

AMENDMENT "C"

APPLICANTS: Masamitsu Ino et al. ATTY DOCKET NO: 09792909-4645
SERIAL NO.: 09/678,459 GROUP ART UNIT: 1725
DATE FILED: October 3, 2000 EXAMINER: Geoffrey Evans
INVENTION: "LASER ANNEALING APPARATUS (As Amended)"

Commissioner for Patents
Box 1450
Alexandria, Virginia 22313-1450

S I R:

This Amendment "C" is filed in response to the Office Action of March 13, 2003. Please reconsider the application in view of the amendment and remarks presented below.

IN THE TITLE OF THE INVENTION

Please replace the Title of the Invention with the following replacement Title of the Invention:

--LASER ANNEALING APPARATUS--

IN THE CLAIMS

Please amend claim 11 as follows:

11. (Twice Amended) A laser annealing apparatus used for fabrication of a thin film semiconductor device integrately formed with a plurality of thin film transistors each of which includes as an active layer a semiconducting thin film which is formed on a surface of an insulating substrate spread in longitudinal and lateral directions across the surface of the insulating substrate and then crystallized, comprising:

means for intermittently irradiating a pulsed laser beam formed in a band-shape along the longitudinal direction of the insulating substrate to the insulating substrate, and simultaneously moving the laser beam relative to the insulating substrate in the lateral direction with a specific movement pitch while partially overlapping regions irradiated with the laser beam to each other, the overlapped portions of the irradiated regions having a band shape along the longitudinal direction, the pulsed laser beam irradiating the semiconducting thin film effecting the semiconducting thin film to spread in a longitudinal and a lateral direction across the surface of the insulating substrate and then crystallize;

06/02/2003 YPOLITE1 00000055 193140 09678459

01 FC:1201

84.00 CH